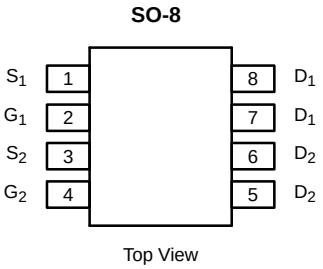
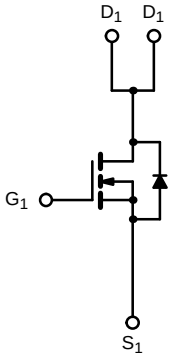
Complimentary 30-V (D-S) MOSFET

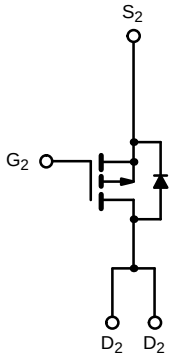
PRODUCT SUMMARY			
	V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
N-Channel	30	0.05 @ V_{GS} = 10 V	± 3.5
		0.07 @ V_{GS} = 6 V	± 3
		0.08 @ V_{GS} = 4.5 V	± 2.5
P-Channel	–30	0.10 @ V_{GS} = –10 V	± 3.5
		0.12 @ V_{GS} = –6V	± 3
		0.16 @ V_{GS} = –4.5 V	± 2.5



Top View



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V_{DS}	30	–30	V
Gate-Source Voltage		V_{GS}	± 20	± 20	
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	± 3.5	± 3.5	A
	T_A = 70°C		± 2.8	± 2.8	
Pulsed Drain Current		I_{DM}	± 20	± 20	
Continuous Source Current (Diode Conduction)[a]		I_S	1.7	–1.7	
Maximum Power Dissipation[a]	T_A = 25°C	P_D	2.0		W
	T_A = 70°C		1.3		
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150		°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	N- or P- Channel	Unit
Maximum Junction-to-Ambient[a]	R_{thJA}	62.5	°C/W

Notes
a. Surface Mounted on FR4 Board, t ≤ 10 sec.

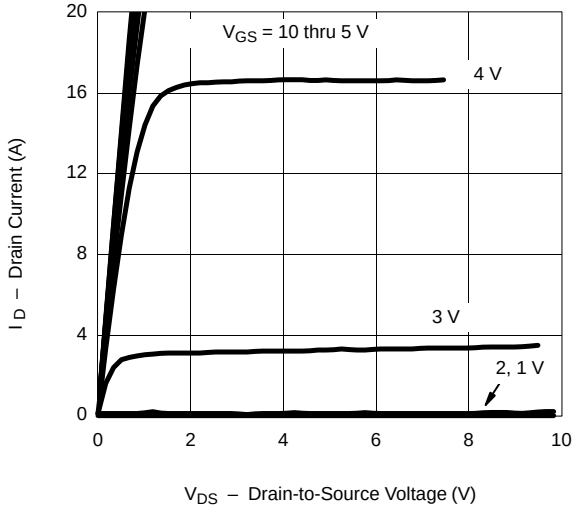
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition		Min	Typ[a]	Max	Unit
Static							
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	N-Ch	1.0			V
		V_{DS} = V_{GS}, I_D = –250 μA	P-Ch	–1.0			
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24 V, V_{GS} = 0 V	N-Ch			1	μA
		V_{DS} = –24 V, V_{GS} = 0 V	P-Ch			–1	
		V_{DS} = 15 V, V_{GS} = 0 V, T_J = 70°C	N-Ch			5	
		V_{DS} = –15 V, V_{GS} = 0 V, T_J = 70°C	P-Ch			–5	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	N-Ch	20			A
		V_{DS} ≤ –5 V, V_{GS} = –10 V	P-Ch	–20			
		V_{DS} ≥ 5 V, V_{GS} = 4.5 V	N-Ch	3.5			
		V_{DS} ≤ –5 V, V_{GS} = –4.5 V	P-Ch	–3.5			
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 3.5 A	N-Ch		0.04	0.05	Ω
		V_{GS} = –10 V, I_D = 3.5 A	P-Ch		0.074	0.10	
		V_{GS} = 6 V, I_D = 3 A	N-Ch		0.045	0.07	
		V_{GS} = – 6 V, I_D = 3 A	P-Ch		0.090	0.12	
		V_{GS} = 4.5 V, I_D = 2.5 A	N-Ch		0.054	0.08	
		V_{GS} = –4.5 V, I_D = 2 A	P-Ch		0.115	0.16	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 3.5 A	N-Ch		9		S
		V_{DS} = –15 V, I_D = –3.5 A	P-Ch		6		
Diode Forward Voltage[b]	V_{SD}	I_S = 1.7 A, V_{GS} = 0 V	N-Ch		0.75	1.2	V
		I_S = –1.7 A, V_{GS} = 0 V	P-Ch		–0.75	–1.2	
Dynamic[a]							
Total Gate Charge	Q_g	N-Channel V_{DS} = 10 V, V_{GS} = 10 V, I_D = 3.5 A P-Channel V_{DS} = –10 V, V_{GS} = –10 V, I_D = –3.5 A	N-Ch		14	35	nC
			P-Ch		14.5	35	
Gate-Source Charge	Q_{gs}		N-Ch		1.9		
			P-Ch		2.7		
Gate-Drain Charge	Q_{gd}		N-Ch		2.8		
			P-Ch		3.5		
Turn-On Delay Time	$t_{d(on)}$	N-Channel V_{DD} = 15 V, R_L = 15 Ω, I_D ≅ 1 A, V_{GEN} = 10 V, R_G = 6 Ω P-Channel V_{DD} = –15 V, R_L = 15 Ω, I_D ≅ –1 A, V_{GEN} = –10 V, R_G = 6 Ω	N-Ch		10	30	ns
			P-Ch		11	30	
Rise Time	t_r		N-Ch		10	40	
			P-Ch		11	40	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		26	50	
			P-Ch		30	50	
Fall Time	t_f		N-Ch		10	50	
			P-Ch		12	50	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 3.5 A, di/dt = 100 A/μs	N-Ch		60	120	
			P-Ch		40	100	

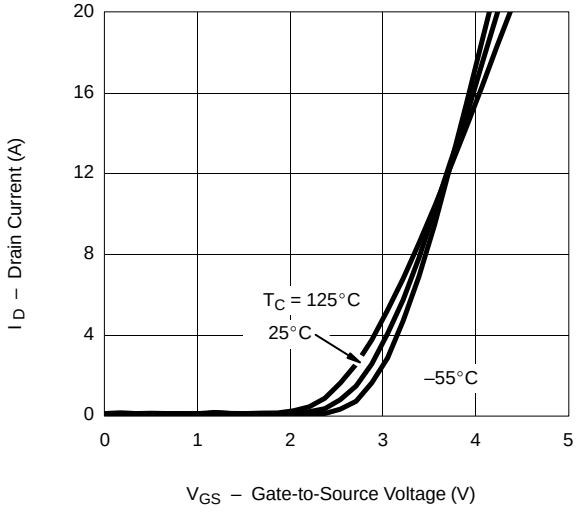
Notes
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) N-CHANNEL

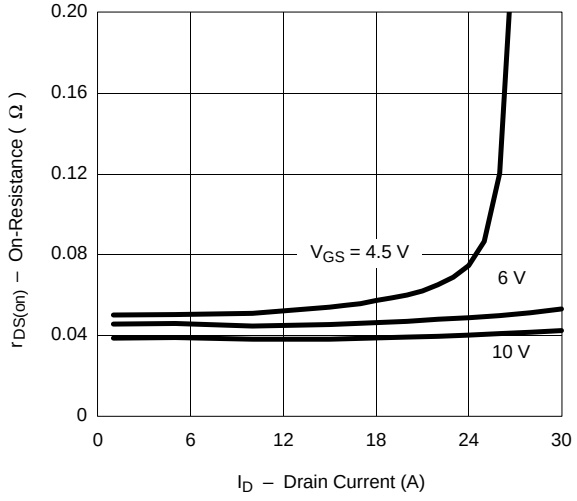
Output Characteristics



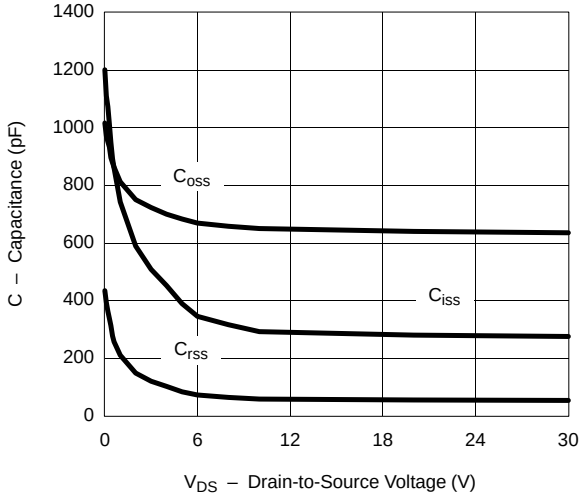
Transfer Characteristics



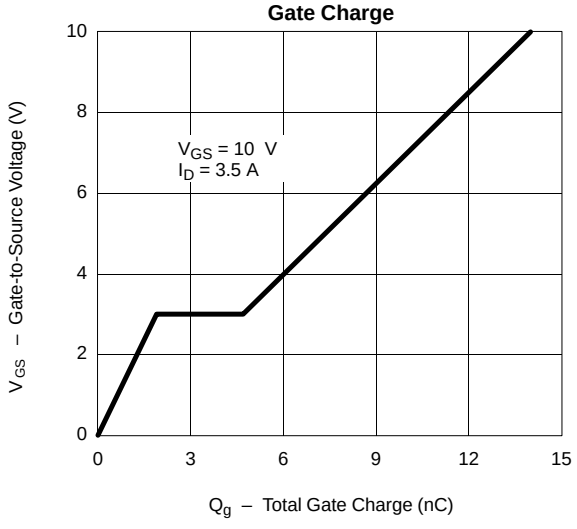
On-Resistance vs. Drain Current



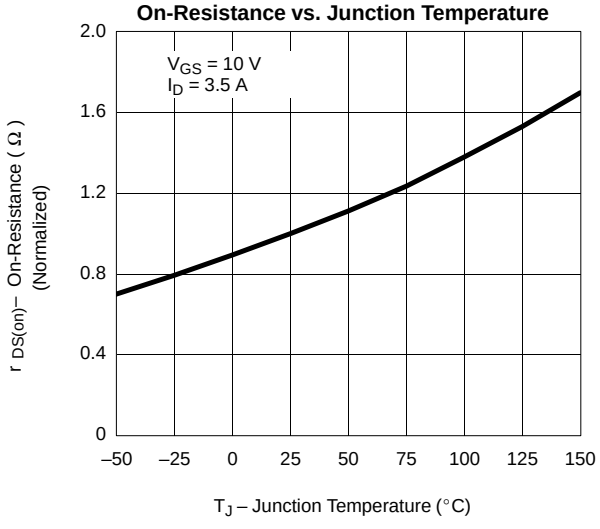
Capacitance



Gate Charge

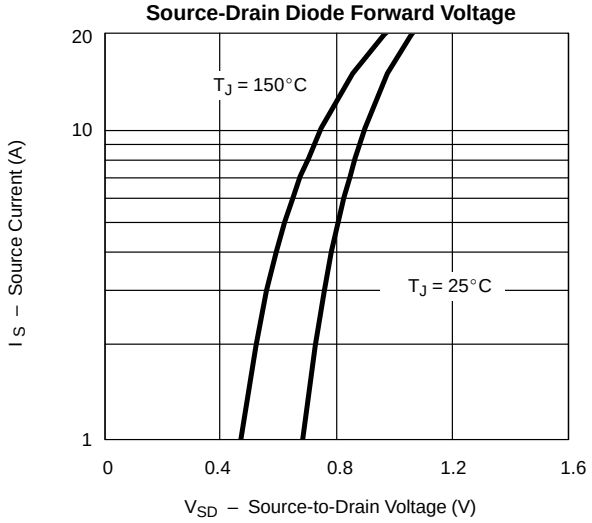


On-Resistance vs. Junction Temperature

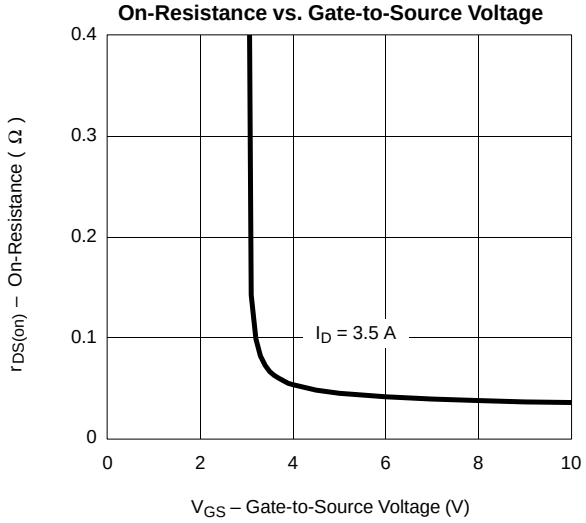


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) N-CHANNEL

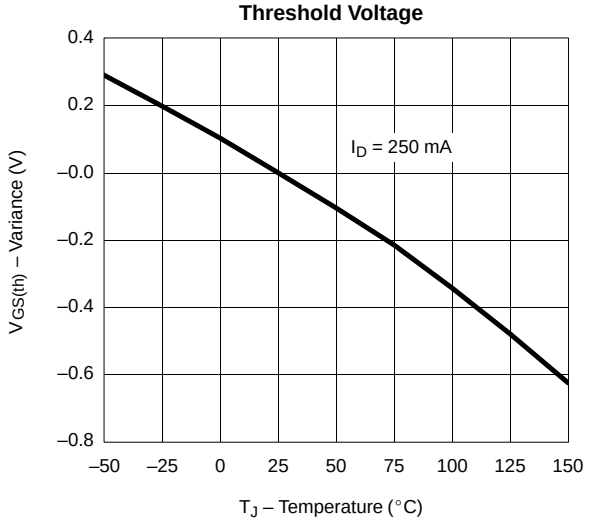
Source-Drain Diode Forward Voltage



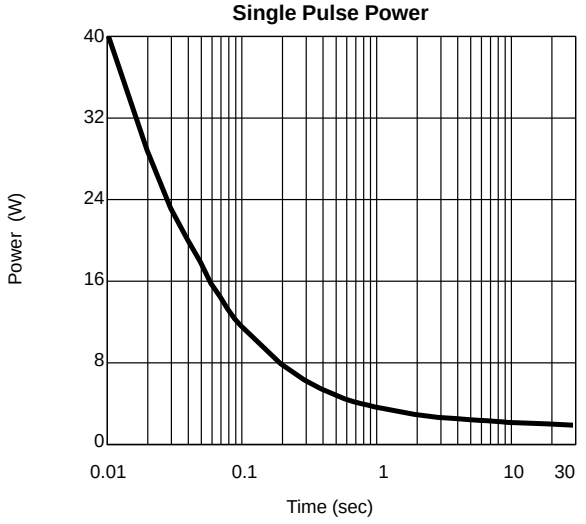
On-Resistance vs. Gate-to-Source Voltage



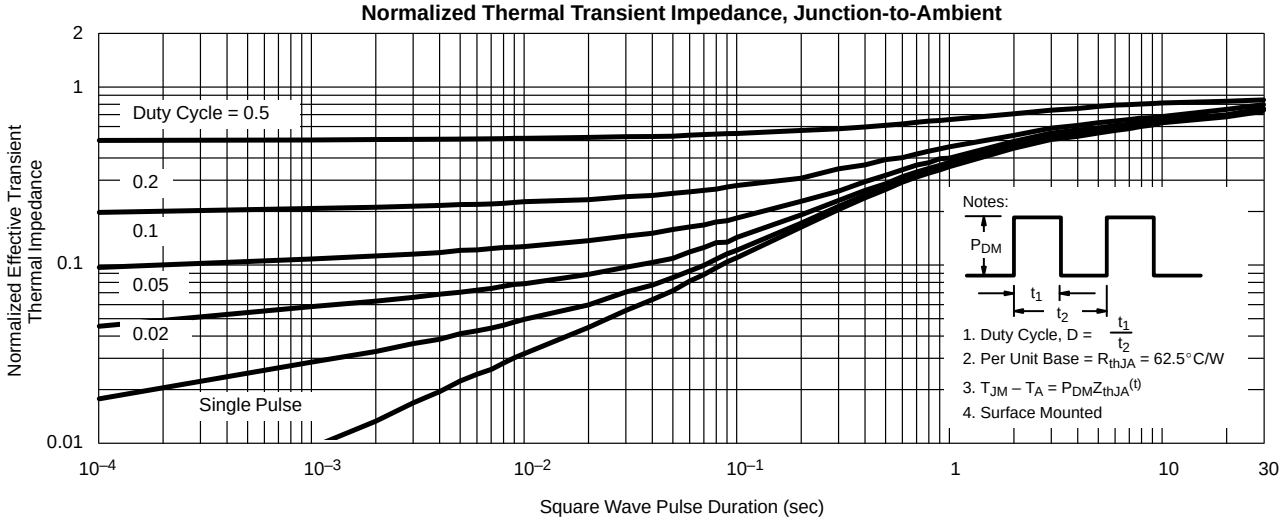
Threshold Voltage



Single Pulse Power

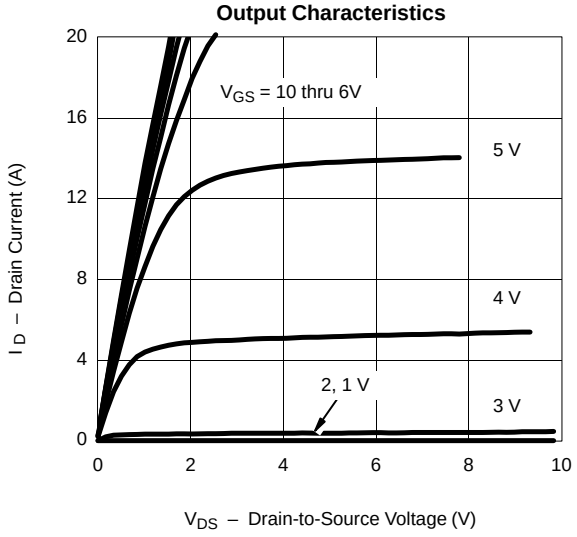


Normalized Thermal Transient Impedance, Junction-to-Ambient

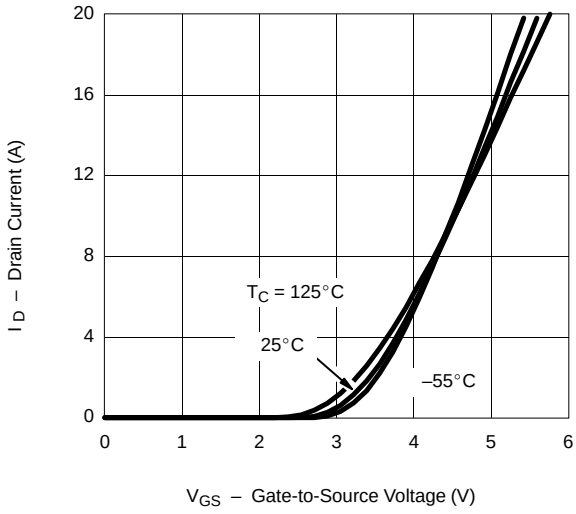


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) P-CHANNEL

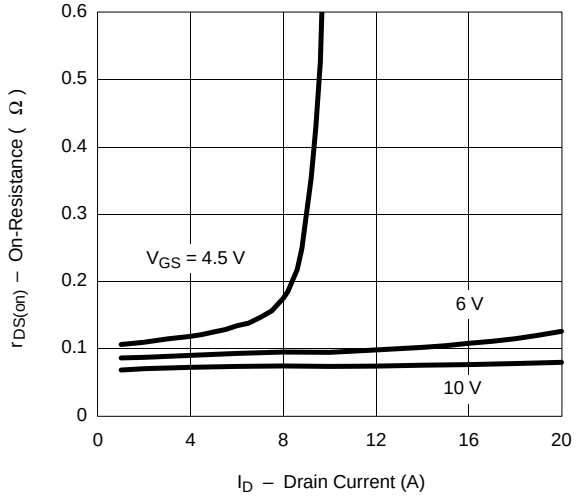
Output Characteristics



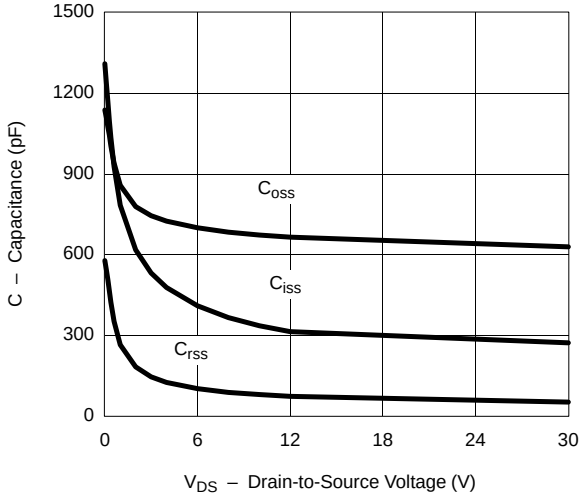
Transfer Characteristics



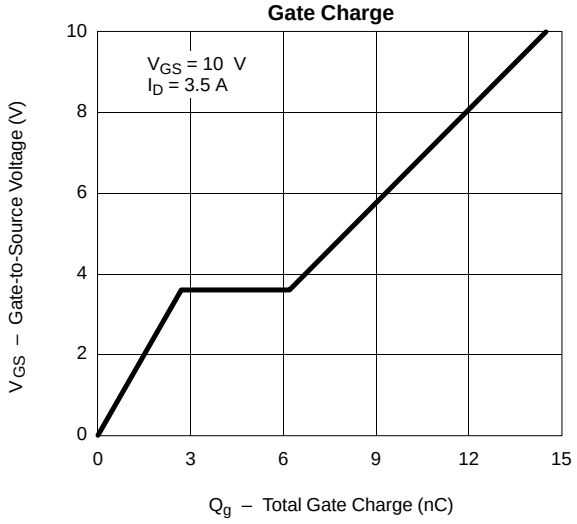
On-Resistance vs. Drain Current



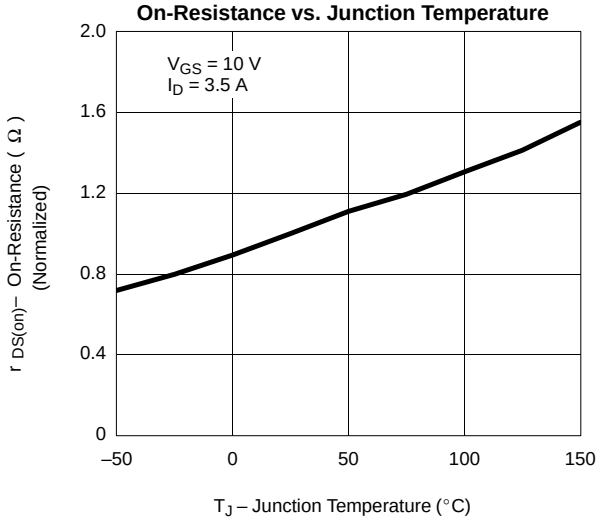
Capacitance



Gate Charge

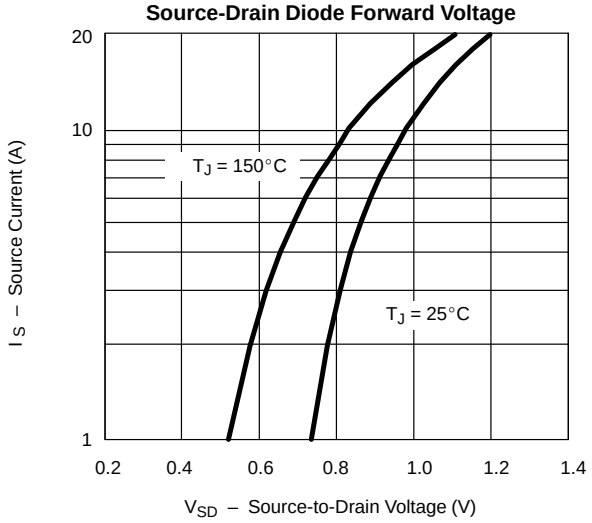


On-Resistance vs. Junction Temperature

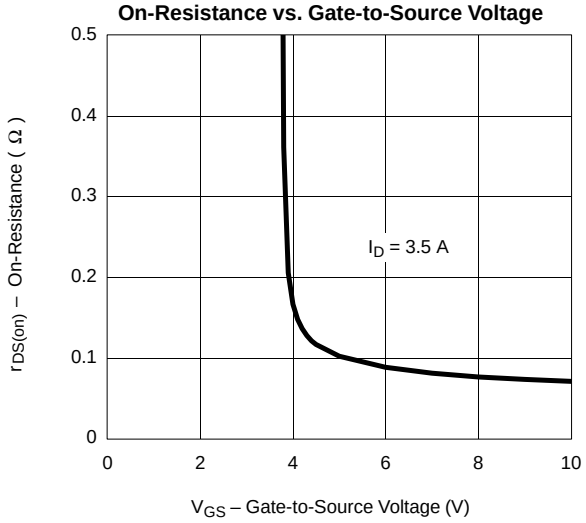


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) P-CHANNEL

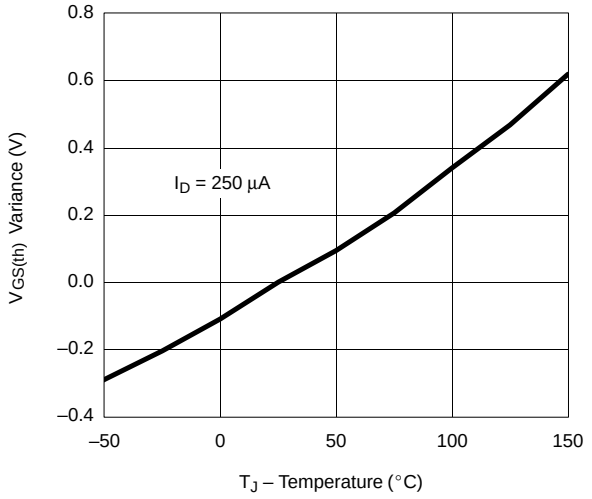
Source-Drain Diode Forward Voltage



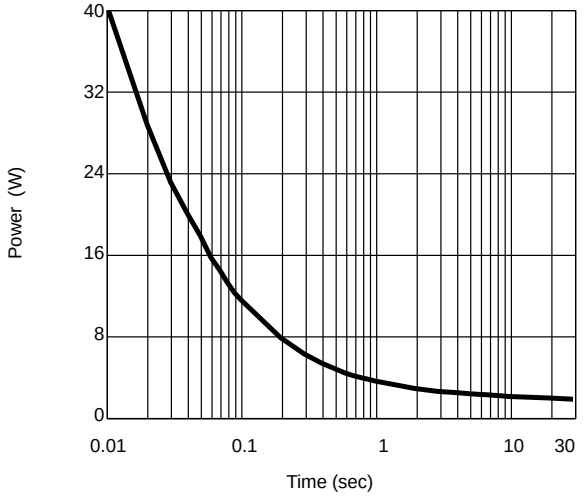
On-Resistance vs. Gate-to-Source Voltage



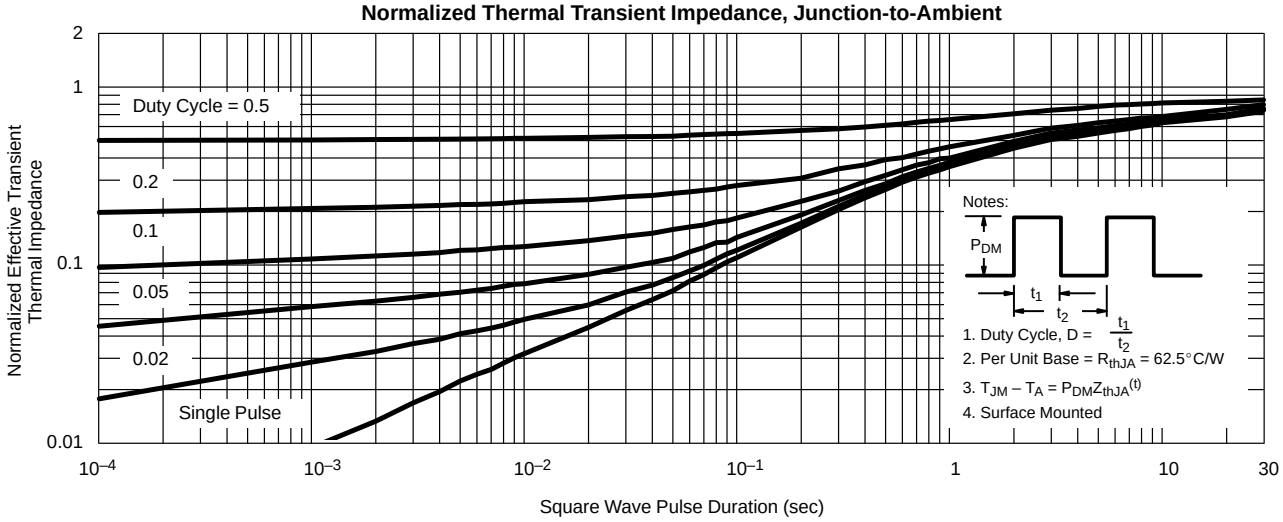
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



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